



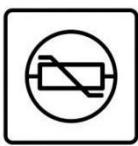
ESD



TVS



TSS



MOV



GDT



PLED

BAT46W-MS

Product specification

Features

- High breakdown voltage
- Low turn-on voltage
- Guard ring construction for transient protection

Reference News

PACKAGE OUTLINE	PIN Configuration	MARKING
 SOD-123		

Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Peak repetitive peak reverse voltage	V _{RRM}	100	V
Working peak reverse voltage	V _{RWM}		
Forward continuous current	I _F	150	mA
Repetitive peak forward current (Note 1) @ tp < 1.0s, Duty Cycle < 50%	I _{FRM}	350	mA
Non-repetitive Peak Forward surge current @ t = 8.3ms	I _{FSM}	750	mA
Power dissipation	P _D	500	mW
Thermal resistance junction to ambient air	R _{θJA}	200	°C/W
Operating Junction Temperature Range	T _j	-40 ~ +125	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

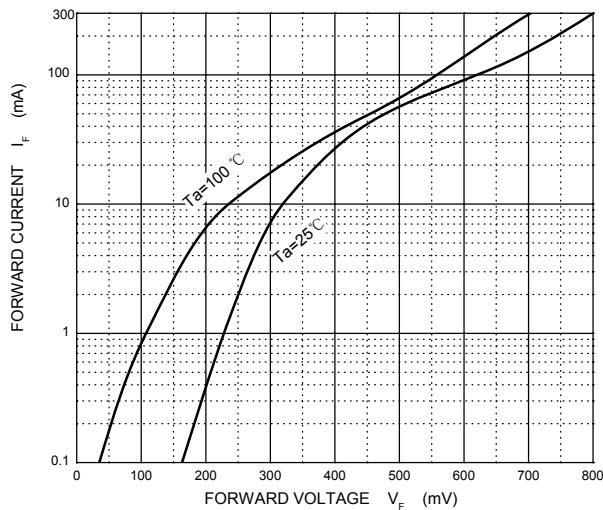
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage(Note 2)	V _R	I _R = 100μA	100			V
Reverse voltage leakage current	I _R	V _{R1} =1.5V			0.3	μA
		V _{R2} =10V			0.5	
		V _{R3} =50V			1	
		V _{R4} =75V			2	
Forward voltage(Note 2)	V _F	I _{F1} =0.1mA			0.25	V
		I _{F2} =10mA			0.45	
		I _{F3} =250mA			1	
Diode capacitance	C _T	V _R =0, f=1MHz		20		pF
		V _R =1V, f=1MHz		12		

Notes: 1. Part mounted on FR-4 board with recommended pad layout.

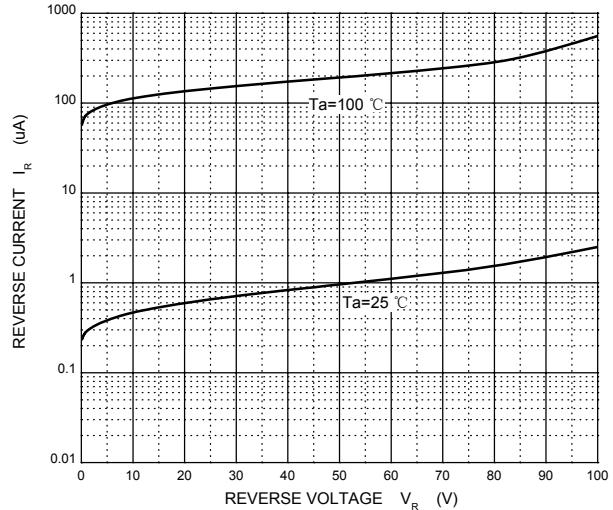
2. Short duration pulse test used to minimize self-heating effect.

Typical Characteristics

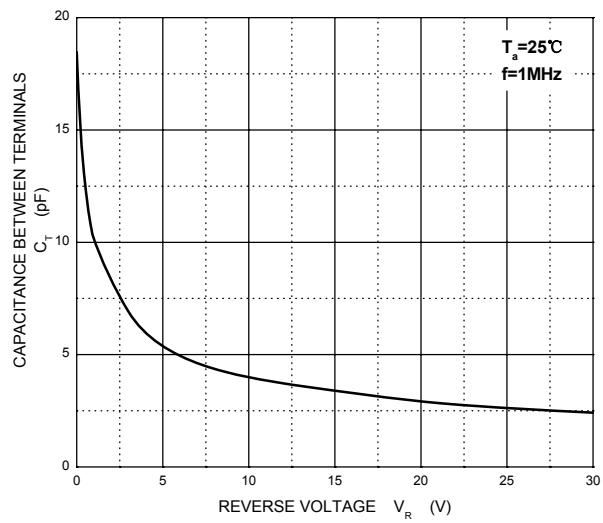
Forward Characteristics



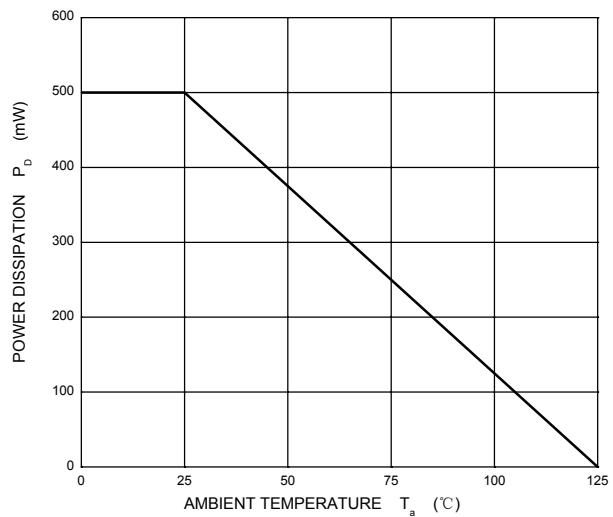
Reverse Characteristics

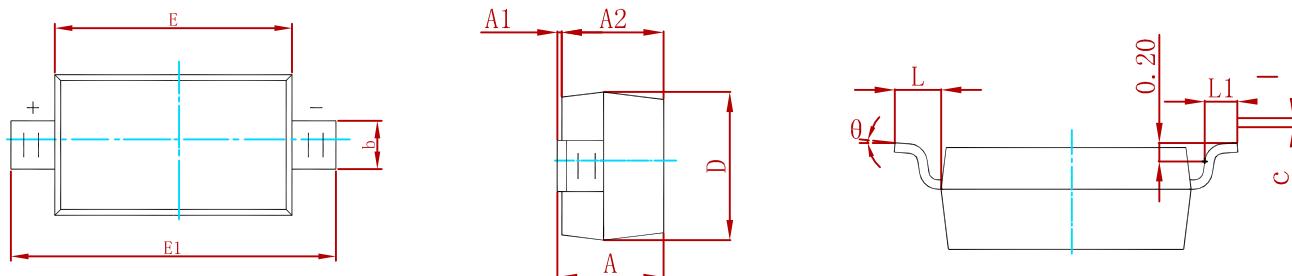


Capacitance Characteristics

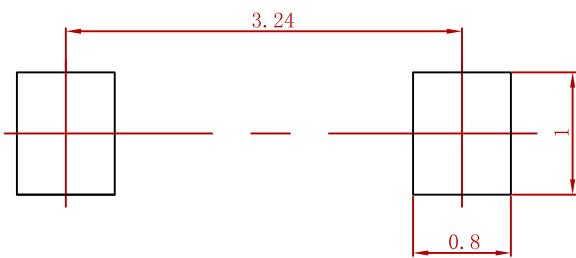


Power Derating Curve



PACKAGE MECHANICAL DATA


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
c	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
E	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500 REF		0.020 REF	
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

REELSPECIFICATION

P/N	PKG	QTY
BAT46W-MS	SOD-123	3000

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